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View Online at https://aerobasegroup.com/nsn/5961-01-338-2175 **Inclosure Material:** Metal **Overall Length:** 1.253 inches **Function For Which Designed:** Rectifier **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-203aa **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case and quality assurance level tx **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 720.0 nonrepetitive peak reverse voltage and 600.0 working peak reverse voltage **Current Rating Per Characteristic:** 12.00 amperes forward current, average absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud **Specification Data:** 81349-mil-s-19500/260 government specification Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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